PNP Transistors Array

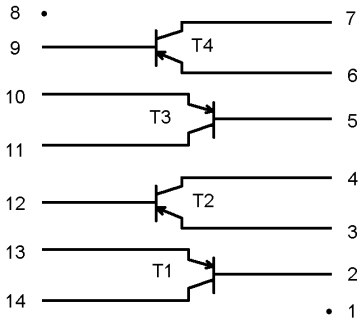
HJ622A

GENERAL DESCRIPTION

The HJ622A is a PNP Transistors Array IC, Pin to pin replaced RUSSIAN IC 2TC622A. It not only have closely Elec-match and excellent Heat-match but also coherence and uniformity is superior to other discrete circuit. Package is Ceramic Flat 14pin, Reliability and relative stability worked in -55℃ ~ + 125℃.

ELECTRIC PRINCIPLE DIAGRAM

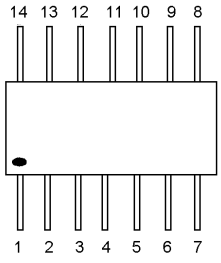
Table 1.



PKG & PIN CONFIGURATION

Table 2.

Ceramic Flat 14pin



Pin NO.	1	2	3	4	5	6	7
FUN	NC	b_1	e_2	c_2	b_3	e_4	c_4
Pin NO.	8	9	10	11	12	13	14
FUN	NC	b_4	e_3	c_3	b_2	e_1	c_1

ABSOLUTE MAXIMUM RATINGS

Voltage of Power Supply: 50V

Dissipation Power: 600mW

OperatingTemperature: -55∽+125℃.

Junction Temperature: +175℃

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ELECTRICAL CHARATERISTICS

-55℃≤T_A≤+125℃ unless otherwise noted.

Table 3.

Parameter	Symbol	Conditions	Ratings			Unit
			Min	Typ	Max	
DC Forward-Current Transfer Ratio	h_{FE}	V_{CE}=5V，I_E=200mA	25	100	150	
Collector-Cutoff Current	I_{CBO}	V_{CB}=45V		0.1	10	A
Collector-Emitter Satiation Voltage	$V_{CE(sat)}$	I_B=80mA,I_C=400mA		0.2	1.3	V
Emitter - Current	I_{EBO}	V_{EB}=4V		0.1	20	A
Base- Emitter Satiation Voltage	$V_{BE(sat)}$	I_B=80mA			1.2	V
Collector-Emitter Breakdown Voltage	BV_{CEO}	I_C=0.1mA	55			V
Current-Gain Bandwidth Product	f_T	V_{CE}=10V，I_C=3mA	200			MHz

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